

## Rad-hard plastic Dual D-type positive edge-triggered flip-flop



#### **Features**

- Dual D-type positive edge-triggered flip-flop
- 6 V max. operating
- 7 V max. rating
- 8.5 ns propagation delay
- Nickel/Palladium/Gold-lead-finished (NiPdAu), whisker-free
- · Gold-wires
- RML <1% and CVCM <0.1% guaranteed outgassing</li>
- 50 krad (Si) Total Ionizing Dose
- SEL-free up to 62.5 MeV.cm²/mg
- Mass: 80 mg
- · Compliant with ST-LEO-specification

#### **Maturity status link**

LEOAC74

### **Applications**

· Low earth orbit (LEO) applications

### **Description**

The LEOAC74 is a CMOS Dual D-type positive edge-triggered flip-flop for use in aerospace environments. It operates from 2 V to 6 V power supply (7 V absolute maximum rating).

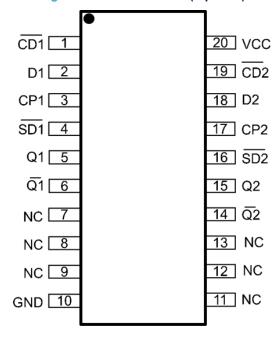
The LEOAC74 can operate over a large temperature range of -40 °C to +125 °C and it is housed in plastic TSSOP-20, Thin-Shrink Small Outline Package, 20 leads, using golden bonding and Nickel/Palladium/Golden-lead-finishing to prevent whiskers.

The LEOAC74 is compliant with ST-LEO-specification, dedicated specification for space-ready rad-hard plastic products. This AEC-Q100-based specification offers a specific trade-off between footprint size savings, cost of ownership and quality assurance together with radiation hardness and large quantity capability.



## Functional description

Figure 1. Pin connections (top view)



NC: not internally connected.

The pin can be externally connected to any potential.

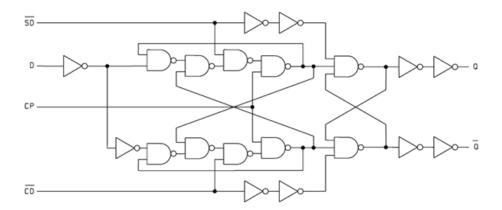


Figure 2. Equivalent schematic

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Table 1. Truth table for each flip-flop

	INP	OUTI	PUTS		
/SD	/CD	СР	D	Q	/Q
L	Н	X	X	Н	L
Н	L	X	X	L	Н
L	L	X	X	H <sup>(1)</sup>	H <sup>(1)</sup>
Н	Н	Rise clock edge	Н	Н	L
Н	Н	Rise clock edge	L	L	Н
Н	Н	L	X	Q0	/Q0

<sup>1.</sup> This configuration is unstable; that is, it does not persist when either SD or CD returns to its inactive (high) level.

H = High voltage level.

L = Low voltage level.

X = Don't care.

Q0 (or /Q0) = Previous Q (or /Q) before low to high transition of clock.

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<sup>\* =</sup> This configuration is unstable; that is, it does not persist when either SD or CD returns to its inactive (high) level.



## 2 Maximum ratings and operating conditions

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V <sub>CC</sub> (1)	Maximum power supply between V <sub>CC</sub> and GND	-0.5 to 7	V
V <sub>IN</sub>	DC input voltage range	-0.5 to V <sub>CC</sub> +0.5 (and 7 V max.)	V
V <sub>OUT</sub>	DC output voltage range	-0.5 to V <sub>CC</sub> + 0.5 (and 7 V max.)	V
I <sub>K</sub>	I/O clamp diode current	+/-20	mA
T <sub>stg</sub>	Maximum temperature storage	-65 to +150	°C
T <sub>j</sub> (2)	Maximum junction temperature	+150	°C
R <sub>th</sub> (3)	Junction to ambient thermal resistance (Oja)	80	°C/W
Inth (3)	Junction to case thermal resistance (Θjc)	17	°C/W
ESD	HBM (human body model)	2k	V

- 1. All voltages, except differential I/O bus voltage, are with respect to the network ground terminal.
- 2. Maximum junction temperature shall not be exceeded except for allowable short duration burn-in screening conditions as per the method 5004 of MIL-STD-883.
- 3. Short-circuits can cause excessive heating. Destructive dissipation can result from short-circuits on the amplifiers.

Note:

Absolute maximum ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. All values are referred to GND.

**Table 3. Operating conditions** 

Symbol	Parameter	Min.	Max.	Unit
V <sub>CC</sub>	Analog supply voltage	2	6	V
V <sub>IN</sub>	Input voltage range	0	V <sub>CC</sub>	V
V <sub>OUT</sub>	Output voltage range	0	V <sub>CC</sub>	V
Та	Ambient temperature range	-40	+125	°C

Note: All unused inputs must be held at VCC or GND to ensure proper device operation.

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### 3 Electrical characteristics

 $V_{CC}$  = 3 V to 5.5 V, typical values are at ambient Ta = +25 °C, min. and max. values are at Ta = -40 °C and +125 °C, unless otherwise specified.

**Table 4. Electrical characteristics.** 

Voh (1)   Vo	Symbol	Parameter	Test condition	VCC (V)	Min.	Тур.	Max.	Unit	
Voh (1)				3	2.9				
VoH (1)					4.4				
VoH (1)			$V_{IN} = V_{CC}$ or GND, $I_{OH} = -50 \mu A$	5.5	5.4				
Vob   Vob   Figh level output voltage   For all inputs affecting output under test, Vin = Vin minimum or Vin maximum. For all other inputs, Vin = Voc or GND, lon = -24 mA   For all inputs affecting output under test, Vin = Vin minimum or Vin maximum. For all other inputs, Vin = Voc or GND lon = -50 mA   S.5   3.85   3.85			minimum or $V_{\text{IL}}$ maximum. For all other inputs,	3	2.4				
Minimum or Vi <sub>L</sub> maximum. For all other inputs, Vi <sub>N</sub> = V <sub>CC</sub> or GND, lo <sub>H</sub> = 24 mA	V <sub>OH</sub> <sup>(1)</sup>	High level output voltage	$V_{IN} = V_{CC}$ or GND, $I_{OH} = -12$ mA					V	
Voc									
Minimum or Vi <sub>IL</sub> maximum. For all other inputs, Vi <sub>IN</sub> = V <sub>CC</sub> or GND I <sub>OH</sub> = -50 mA   3.85   0.1			V <sub>IN</sub> = V <sub>CC</sub> or GND, I <sub>OH</sub> = -24 mA	5.5	4.7				
For all inputs affecting output under test, V <sub>IN</sub> = V <sub>IH</sub> minimum or V <sub>IL</sub> maximum. For all other inputs, V <sub>IN</sub> = V <sub>CC</sub> or GND, I <sub>OL</sub> = +50 µA   5.5   0.1			minimum or V <sub>IL</sub> maximum. For all other inputs,	5.5	3.85				
Vol. (1)   Vol. (1)   Low level output voltage   Vin = Voc. or GND, IoL = +50 μA   4.5   0.1			65 6	3			0.1		
$V_{OL}^{(1)} = V_{CC} \text{ or GND, } I_{OL} = +50 \text{ $\mu$A} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For all inputs affecting output under test, } V_{IN} = V_{IH} \\ \hline For$									
$V_{OL}^{(1)} \begin{tabular}{l l l l l l l l l l l l l l l l l l l $			$V_{IN}$ = $V_{CC}$ or GND, $I_{OL}$ = +50 $\mu$ A						
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		Low level output voltage							
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Vo. (1)		$V_{IN} = V_{CC}$ or GND, $I_{OL} = +12$ mA					V	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	▼OL			4.5			0.5	v	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$			V <sub>IN</sub> = V <sub>CC</sub> or GND, I <sub>OL</sub> = +24 mA	5.5			0.5		
Note   High level output current   3   -12   4.5   -24   5.5   -24   6.5   -24   7.5   7			minimum or V <sub>IL</sub> maximum. For all other inputs,	5.5			1.65	-	
High level output current			V <sub>IN</sub> = V <sub>CC</sub> or GND, I <sub>OL</sub> = +50 mA		10				
Solution		Library and and an annual							
Column   C	ІОН	High level output current							
I <sub>OL</sub> Low level output current     4.5     24       V <sub>IH</sub> (2)     High level input voltage     3     2.1     3       V <sub>IL</sub> (2)     4.5     3.15     mA       5.5     3.85     3     0.9       V <sub>IL</sub> (2)     Low level input voltage     4.5     1.35     V					-24		40	mA	
V <sub>IH</sub> (2)     High level input voltage     3     2.1     3     2.1     4.5     3.15     mA       V <sub>IL</sub> (2)     Low level input voltage     3     0.9     4.5     1.35     V	la.	Low lovel output ourrent							
V <sub>IH</sub> (2)     High level input voltage     3     2.1     mA       4.5     3.15     mA       5.5     3.85       V <sub>IL</sub> (2)     Low level input voltage     3     0.9       4.5     1.35     V	IOL	Low level output current							
V <sub>IH</sub> (2)     High level input voltage     4.5     3.15     mA       5.5     3.85     3     0.9       V <sub>IL</sub> (2)     Low level input voltage     4.5     1.35     V	V <sub>IH</sub> <sup>(2)</sup> High le				2.1		24		
5.5     3.85       V <sub>IL</sub> (2)     Low level input voltage       3     0.9       4.5     1.35       V		High level input voltage						mA	
V <sub>IL</sub> <sup>(2)</sup> Low level input voltage         3         0.9           4.5         1.35         V		g is to impact to image							
V <sub>IL</sub> <sup>(2)</sup> Low level input voltage 4.5 1.35 V					2.00		0.9		
	V <sub>II</sub> <sup>(2)</sup>	Low level input voltage						V	
1 0:0   1:00				5.5			1.65	-	

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Symbol	Parameter	Test condition	VCC (V)	Min.	Тур.	Max.	Unit
V <sub>IC+</sub>	Positive input clamp voltage	For input under test, I <sub>IN</sub> = -1.0 mA	0	0.4		1.5	V
V <sub>IC</sub> -	Negative input clamp voltage	For input under test, I <sub>IN</sub> = -1.0 mA	Open	0.4		-1.5	V
I <sub>IH</sub>	Input current high	For input under test, $V_{IN} = V_{CC}$ . For all other inputs, $V_{IN} = V_{CC}$ or GND	5.5			1	μA
I <sub>IL</sub>	Input current low	For input under test, $V_{IN}$ = GND. For all other inputs, $V_{IN}$ = $V_{CC}$ or GND	5.5			-1	μA
I <sub>CCH</sub>	Quiescent supply current, output high	For all inputs, V <sub>IN</sub> = V <sub>CC</sub> or GND I <sub>OUT</sub> = 0 A	5.5			40	μA
I <sub>CCL</sub>	Quiescent supply current, output low	For all inputs, V <sub>IN</sub> = V <sub>CC</sub> or GND I <sub>OUT</sub> = 0 A	5.5			40	μA
C <sub>IN</sub> (3)	Input capacitance	Ta = +25 °C	5			10	pF
C <sub>PD</sub> (3) (4)	Power dissipation capacitance	Ta = +25 °C, F = 1 MHz	5			88	pF
		C <sub>L</sub> = 2 pF, R <sub>L</sub> = 500 ohm (see Figure 3)	3		3.7		
$T_r$ , $T_f$	Output rise time and fall	ot - 2 pr, rt - 300 onin (see righte 3)	4.5		2.0		ns
11, 11	time	C <sub>L</sub> = 50 pF, R <sub>L</sub> = 500 ohm (see Figure 3)	3		5.2		115
		C <sub>L</sub> = 50 μr, κ <sub>L</sub> = 500 onm (see Figure 3)	4.5		4.5		
T <sub>PHL</sub> <sup>(5)</sup>	Propagation delay time An	C <sub>1</sub> = 50 pF, R <sub>1</sub> = 500 ohm (see Figure 3)	3	1		11.5	
PHL * /	to Yn, high to low	or or privile - soo orminace righte sy	4.5	1		8.5	ns
T <sub>PLH</sub> <sup>(5)</sup>	Propagation delay time An	C <sub>1</sub> = 50 pF, R <sub>1</sub> = 500 ohm (see Figure 3)	3	1		12.5	115
I PLH <sup>(o)</sup>	to Yn, low to high	ο <sub>L</sub> = 30 μι, τις = 300 σππ (see rigure 3)	4.5	1		9	

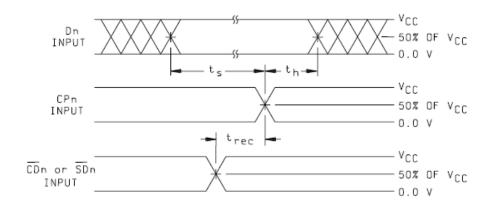
- 1. The  $V_{OH}$  and  $V_{OL}$  tests shall be tested at  $V_{CC}$  = 3.0 V and 4.5 V. The  $V_{OH}$  and  $V_{OL}$  tests are guaranteed, if not tested, for other values of  $V_{CC}$ . Limits shown apply to operation at  $V_{CC}$  = 3.3 V, ±0.3 V and  $V_{CC}$  = 5.0 V ±0.5 V. Tests with input current at +50 mA and –50 mA are performed on only one input at a time with duration not to exceed 10 ms. Transmission driving tests may be performed using  $V_{IN}$  =  $V_{CC}$  or GND is used, the test is guaranteed for  $V_{IN}$  =  $V_{IH}$  minimum and  $V_{IL}$  maximum.
- 2. The  $V_{IH}$  and  $V_{IL}$  tests are not required if applied as forcing functions for  $V_{OH}$  and  $V_{OL}$  tests.
- 3. C<sub>IN</sub> and C<sub>PD</sub> shall be measured only for initial qualification and after process or design changes which may affect capacitance. C<sub>IN</sub> shall be measured between the designated terminal and GND at a frequency of 1 MHz. C<sub>PD</sub> shall be tested in accordance with the latest revision of JEDEC Standard JESD20 and table IA herein. For C<sub>IN</sub> and C<sub>PD</sub>, test all applicable pins on five devices with zero failures.
- 4. Power dissipation capacitance ( $C_{PD}$ ) determines both the power consumption ( $P_D$ ) and dynamic current consumption ( $P_D$ ). Where:  $P_D = (C_{PD} + C_L) (V_{CC} \times V_{CC}) f + (I_{CC} \times V_{CC}) and IS = (C_{PD} + C_L) V_{CC} \times f + I_{CC}$ , and f is the frequency of the input signal and  $P_D$  is the external output load capacitance.
- 5. For propagation delay tests, all paths are tested. The AC limits at  $V_{\rm CC}$  = 5.5 V are equal to the limits at  $V_{\rm CC}$  = 4.5 V and guaranteed by testing at  $V_{\rm CC}$  = 4.5 V. The AC limits at  $V_{\rm CC}$  = 3.6 V are equal to the limits at  $V_{\rm CC}$  = 3.0 V and guaranteed by testing at  $V_{\rm CC}$  = 3.0 V. Minimum AC limits for  $V_{\rm CC}$  = 5.5 V and  $V_{\rm CC}$  = 3.6 V are 1.0 ns and guaranteed by guard banding the  $V_{\rm CC}$  = 4.5 V and  $V_{\rm CC}$  = 3.0 V minimum limits, respectively, to 1.5 ns. For propagation delay tests, all paths must be tested.

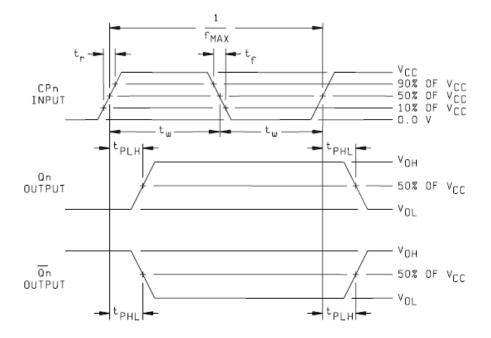
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## 4 Waveform and test circuit

Figure 3. Switching waveforms





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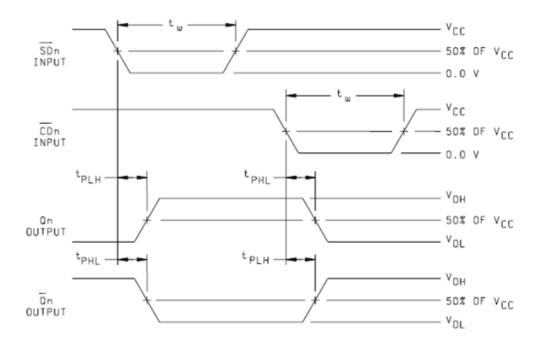
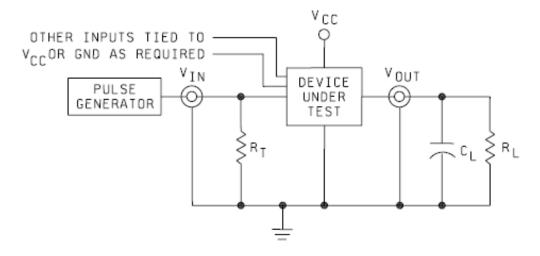


Figure 4. Switching wave forms (continued)

Figure 5. Test circuit



Note:

- V<sub>TEST</sub> = open for t<sub>PLH</sub> and t<sub>PHL</sub>.
- $C_L = 50 p_F$  or equivalent (includes probe and jig capacitance).
- $R_L = 500$ -ohm or equivalent.
- Input signal from pulse generator:  $V_{IN}$  = 0.0 V to  $V_{CC}$ ;  $P_{RR}$  < 1 MHz; ZO = 50-ohm; tr < 3.0 ns; tf < 3.0 ns; tr and tf shall be measured from 10% of  $V_{CC}$  to 90% of  $V_{CC}$  and from 90% of  $V_{CC}$  to 10% of  $V_{CC}$ , respectively; duty cycle = 50 percent.
- Timing parameters shall be tested at a minimum input frequency of 1 MHz.
- The outputs are measured one at a time with one transition per measurement.

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### 5 Radiations

#### Total ionizing dose (TID):

For the qualification, the product is characterized in TID as per MIL-STD-883 TM 1019 up to 50 krad(Si) on 5 biased parts at high dose rate, such a rate being the worst condition for a pure CMOS technology.

All parameters provided in Table 1 apply to both pre- and post-irradiation.

Each new production lot is tested at high dose rate as per MIL-STD-883 TM 1019 on 5 parts.

#### Heavy-ions:

Single Event Latchup (SEL) is characterized at 125 °C at a LET of 62.5 MeV.cm2/mg. The test shows the product is immune to heavy ions at this LET. Heavy-ion trials are performed on qualification lots only.

The results in radiation are summarized in table 5 as follows.

Table 5. Radiations

Туре	Conditions	Results
TID <sup>(1)</sup>	<ul> <li>High-dose rate (40 krad (Si) / h)</li> <li>Temperature: 25 °C</li> <li>Performed on 5 biased parts</li> </ul>	Within Table 1 up to 50 krad(Si)
SEL <sup>(2)</sup>	<ul> <li>LET: 62.5 MeV.cm2/mg (Xenon ions)</li> <li>Temperature: 125 °C</li> <li>Fluence: 1 x 10<sup>7</sup> ions/cm<sup>2</sup> (10 Million of particles per cm<sup>2</sup>)</li> <li>Normal incidence</li> </ul>	Immune to SEL up to 62.5 MeV.cm <sup>2</sup> /mg

<sup>1.</sup> A total ionizing dose (TID) of 50 krad(Si) is equivalent to 500 Gy(Si), (1 gray = 100 rad).

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<sup>2.</sup> SEL: single event latch-up.



## 6 Outgassing

Specification (tested per ASTM E 595)	Value	Unit
Recovered mass loss (RML) (1)	0.06	%
Collected volatile condensable material (CVCM) (2)	0.00	%

- 1. RML < 1%
- 2. CVCM < 0.1%

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## 7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

### 7.1 TSSOP-20 package information

Figure 6. TSSOP-20 Mechanical drawing

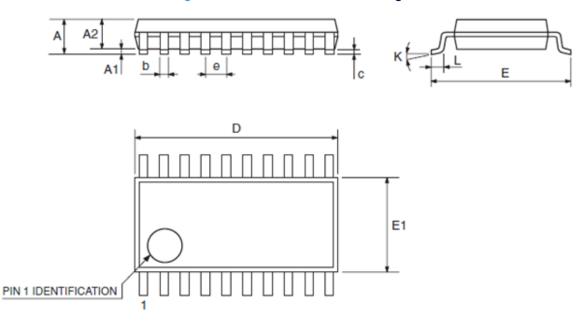


Table 6. TSSOP-20 package mechanical data

Symbol		Milimeters			Inches <sup>(1)</sup>	
Symbol	Min.	Тур.	Max.	Min	Тур	Max
Α			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		
С	0.09		0.20	0.004		
D	6.4	6.5	6.6	0.252	0.256	0.260
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
е		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

Note: TSSOP: Thin-Shrink Small Outline Package, using golden bonding and Nickel/Palladium/Golden-lead-finishing.

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### 7.2 TSSOP-20 packing information

C(d)=Ø10.0±0.2 C(e)=Ø44.00(R/eft.) E=12.0±0.5 A=Ø13±0.2 F=20(max.)(Ref: B=2±0.5 0 0 0 C(a)=Ø21±0.8 W3 (Includes flange distortion at outer edge) C(b)158(Ref.) T(b)=1.20±0.15 C(c)=70(Ret// W2 ₹ --0-00.09@=D T(a)=1.00±0.15 0-00.081&=a H3=3.00±0.2 (Date code area) Ref. 856(R = HZ=5.00±0.2 EIAJ-RRMXXB nim8t=8L C(f)=3±0.5 H1=4.00±0.2

Figure 7. TSSOP-20 Carrier tape (dimensions in mm)

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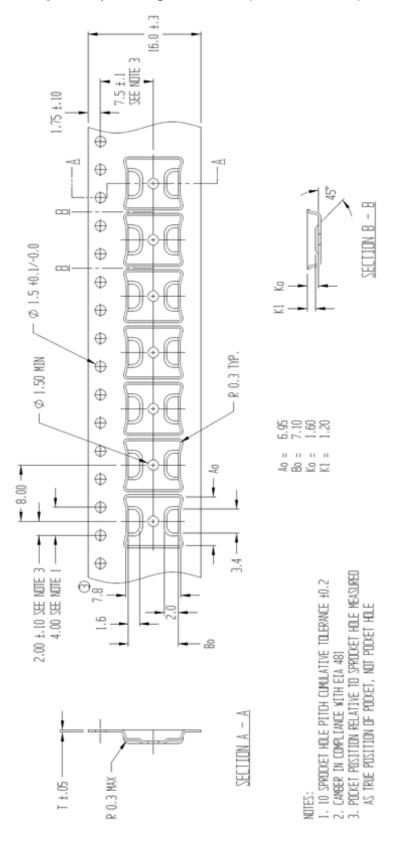


Figure 8. Tape drawing for TSSOP-20 (dimensions in mm)

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## 8 Ordering information

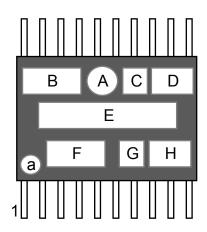
**Table 7. Ordering information** 

Order code	Quality level	Package	Lead-finish	Marking	Packing
LEOAC74PT-D	Development sample	TSSOP-20	NiPdAu	DLEOAC74	Tape and reel
LEOAC74PT	Flight model	TSSOP-20	NiPdAu	LEOAC74	Tape and reel

Table 8. Order code

LEO	AC74	Р	Т
LEO qualification	Name	TSSOP-20 package	Tape and reel

Figure 9. TSSOP20 Marking



- a: pin-1 reference
- A: Second Level of interconnexion (type of lead-finishing)
- B: ST logo
- C: Assy plant
- D: Lot code
- E: Marking area
- F: Country of origin
- G: Assy year
- H: Assy week

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## **Revision history**

Table 9. Document revision history

Date	Version	Changes
10-Jan-2022	1	First release.
31-Jan-2022	2	Removed footnote in Table 7. Ordering information.

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